



# Product data sheet

www.msksemi.com







#### Features

- -30V,-3.0A, RDS(ON) =85mΩ@VGS = 10V
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

#### **Applications**

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

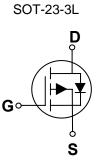
BVDSS	RDSON	ID
-30V	$85 m\Omega$	-3.0A

#### Absolute Maximum Ratings Tc=25 unless otherwise noted

Symbol	Parameter	Rating	Units
Vds	Drain-Source Voltage	-30	V
Vgs	Gate-Source Voltage	±12	V
1_	Drain Current – Continuous (T₄=25℃)	-3.0	A
D	Drain Current – Continuous (T <sub>A</sub> =70°C)	-2.0	A
Ідм	Drain Current – Pulsed <sup>1</sup>	-12.0	A
D	Power Dissipation (T <sub>A</sub> =25°C)	1.56	W
PD Power Dissipation – Derate above 25°C		0.012	W/°C
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		80	°C/W





#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , Ip=-250uA	-30			V
△ BV <sub>DSS</sub> / △ T <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25℃ , I⊳=-1mA		-0.02		V/°C
	Drain Course Lookens Current	Vds=-27V , Vgs=0V , Tj=25°C			- 1	uA
loss	Drain-Source Leakage Current	V⊳s=-24V , V₀s=0V , Tյ=125℃			- 10	uA
lgss	Gate-Source Leakage Current	Vgs= ±12V, Vds=0V			±100	nA

#### **On Characteristics**

Basian		Vgs=-10V , Id=-2A		85	140	mΩ
RDS(ON)	Static Drain-Source On-Resistance	Vgs=-4.5V , Id=-1A		140	180	mΩ
VGS(th)	Gate Threshold Voltage		-0.5	-1.0	<b>-</b> 1.5	V
${}^{\vartriangle}V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	Vgs=Vds , Id =-250uA		-2.8		mV/°C
gfs	Forward Transconductance	Vds=-10V , Id=-1A		3		S

#### **Dynamic and switching Characteristics**

Qg	Total Gate Charge <sup>2,3</sup>		 2.5	
Qgs	Gate-Source Charge <sup>2,3</sup>	VDS=-24V , VGS=-4.5V , ID=-2A	 0.1	 nC
Qgd	Gate-Drain Charge <sup>2,3</sup>		 1.8	
Td(on)	Turn-On Delay Time <sup>2 , 3</sup>		 6.1	
Tr	Rise Time <sup>2,3</sup>	VDD=-15V , VGS=-10V , RG=6Ω	 8.7	
Td(off)	Turn-Off Delay Time <sup>2,3</sup>	ID=-1A	 33.2	 ns
Tf	Fall Time <sup>2,3</sup>		 3.7	
Ciss	Input Capacitance		 226	
Coss	Output Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , F=1MHz	 39	 pF
Crss	Reverse Transfer Capacitance		 29	

### **Drain-Source Diode Characteristics and Maximum Ratings**

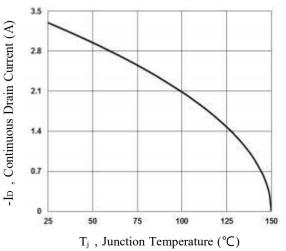
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current				-3.0	А
lsм	Pulsed Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-6.0	А
Vsd	Diode Forward Voltage	Vgs=0V , Is= <b>-</b> 1A , Tյ=25℃			- 1.2	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.2. The data tested by pulsed , pulse width  $\leq 300$  us , duty cycle  $\leq 2\%$ .

3. Essentially independent of operating temperature.







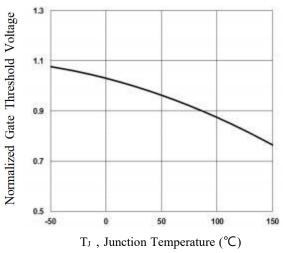
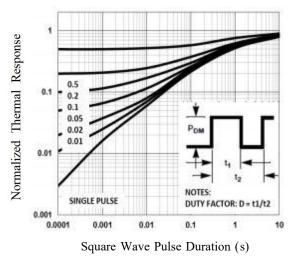
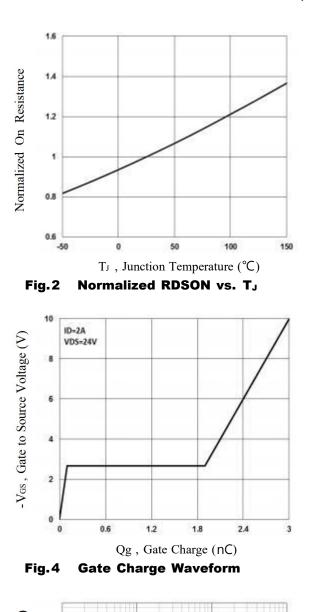


Fig. 3 Normalized V<sub>th</sub> vs. T<sub>J</sub>





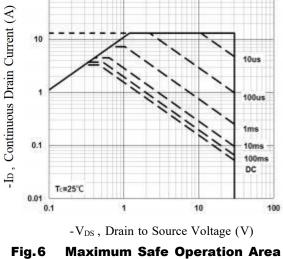


A

Semiconductor

HF

Compiance



www.msksemi.com





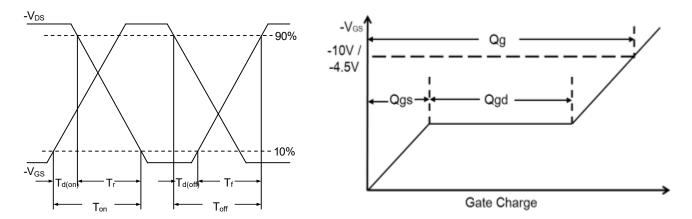


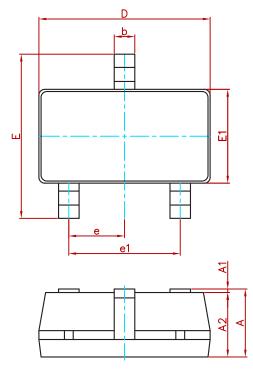
Fig. 7 Switching Time Waveform

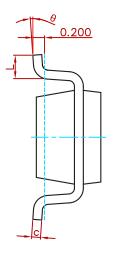
Fig. 8 Gate Charge Waveform





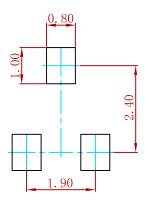
## PACKAGE MECHANICAL DATA





Symbol	Dimensions In Millimeters		Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(	BSC)	0.037	(BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

## Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
AO3403	SOT-23-3L	3000





# <u>Attention</u>

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications f any and all MSKSEMI Semiconductor products described orcontained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuits for safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by MSKSEMI manufacturer:

Other Similar products are found below :

IRFD120 JANTX2N5237 2SK2267(Q) BUK455-60A/B TK100A10N1,S4X(S MIC4420CM-TR VN1206L NDP4060 SI4482DY IRS2092STRPBF-EL IPS70R2K0CEAKMA1 TK31J60W5,S1VQ(O TK31J60W,S1VQ(O TK16J60W,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1 DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1 MCQ7328-TP SSM3J143TU,LXHF DMN12M3UCA6-7 PJMF280N65E1\_T0\_00201 PJMF380N65E1\_T0\_00201 PJMF280N60E1\_T0\_00201 PJMF600N65E1\_T0\_00201 PJMF900N60E1\_T0\_00201